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Two-Dimensional Materials Beyond Graphene: Properties and Device Applications

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ABSTRACT

Two-dimensional (2D) materials beyond graphene have gained significant attention due to their exceptional electronic, optical, and mechanical properties, making them promising candidates for next-generation nanoelectronics and optoelectronic applications. Transition metal dichalcogenides (TMDs), black phosphorus (BP), MXenes, and silicene exhibit unique bandgap tunability, high carrier mobility, and strong light-matter interactions, which overcome graphene's limitations, such as its lack of an intrinsic bandgap. This paper explores the synthesis, properties, and device applications of these advanced 2D materials. Various fabrication techniques, including chemical vapor deposition (CVD), mechanical exfoliation, and solution processing, are discussed in detail.

An experimental investigation is conducted to analyze the electronic transport and optical properties of MoS_2, WS_2, BP, and MXenes. Electrical measurements reveal high on/off current ratios in TMD-based transistors, while photoluminescence studies confirm the bandgap tunability of these materials. Additionally, Raman spectroscopy, X-ray diffraction (XRD), and scanning electron microscopy (SEM) provide insight into structural integrity and surface morphology. The study further explores applications in field-effect transistors (FETs), photodetectors, quantum computing, and energy storage. Despite promising advancements, challenges such as scalability, stability, and integration with existing semiconductor technologies remain.

This review highlights recent breakthroughs in experimental techniques and computational modeling, which pave the way for novel 2D material-based devices. The findings underscore the potential of these materials in revolutionizing nanoelectronics and photonics, with prospects for future research in room-temperature superconductivity, spintronics, and AI-driven material discovery.

Keywords: Solid state physics, carbide, quantum principles

2. INTRODUCTION

2.1 Background on Graphene and Its Limitations

Since its isolation in 2004, graphene has revolutionized the field of nanomaterials due to its exceptional electrical, mechanical, and thermal properties. This single layer of carbon atoms arranged in a honeycomb lattice exhibits ultra-high carrier mobility, excellent mechanical strength, and superior thermal conductivity, making it an ideal candidate for various electronic and optoelectronic applications. However, despite its remarkable attributes, graphene has several intrinsic limitations that hinder its direct implementation in semiconductor and device technologies. One of the primary challenges is the absence of a natural bandgap, which restricts its use in digital logic circuits that require high on/off current ratios. While techniques such as chemical functionalization and substrate engineering have been explored to induce a bandgap in graphene, they often compromise its electronic performance. Additionally, graphene's strong electron-electron interactions and high carrier mobility lead to excessive leakage currents, further limiting its effectiveness in transistor applications.

2.2 Need for Alternative 2D Materials

Given the limitations of graphene, the search for alternative 2D materials with tunable electronic and optical properties has gained significant momentum. Transition metal dichalcogenides (TMDs), black phosphorus (BP),

MXenes, silicene, germanene, and other layered materials have emerged as promising candidates for next-generation electronics, photonics, and quantum computing. Unlike graphene, many of these materials exhibit a direct or tunable bandgap, which is essential for applications in transistors, photodetectors, and energy storage. For example, TMDs such as MoS_2, WS_2, and $MoSe_2$ possess bandgaps ranging from 1 to 2 eV, making them suitable for field-effect transistors (FETs) and optoelectronic devices. Similarly, black phosphorus, with its high anisotropic mobility and thickness-dependent bandgap, offers unique advantages for infrared photonics and flexible electronics.

Apart from their electronic benefits, these materials also exhibit strong spin-orbit coupling, high mechanical flexibility, and compatibility with existing semiconductor fabrication techniques. As research into 2D materials advances, the focus has expanded toward integrating these materials into scalable and commercially viable technologies. Understanding their synthesis, characterization, and functional properties is crucial for overcoming existing technological barriers and unlocking new applications in nanoelectronics, energy storage, and quantum technologies.

2.3. Overview of Research Objectives and Paper Structure

The primary objective of this paper is to explore and critically evaluate two-dimensional (2D) materials that extend beyond graphene, focusing on their unique properties and potential for device applications in nanoelectronics and optoelectronics. In doing so, the research aims to address key questions: How do these emerging 2D materials compare with graphene in terms of electronic, optical, and mechanical performance? What novel synthesis and characterization techniques are employed to harness their properties? And how can these materials be integrated into practical device architectures?

To achieve these objectives, the paper is organized into several key sections. The **Literature Review** (Section 3) surveys the evolution of 2D materials beyond graphene, detailing historical developments, synthesis methods, and a comparison of their properties with those of graphene. **Section 4** presents an in-depth **Experimental Study** where specific 2D materials—such as transition metal dichalcogenides, black phosphorus, and MXenes—are synthesized and characterized using techniques like chemical vapor deposition, Raman spectroscopy, and electron microscopy. This section highlights the material preparation, methodology, and experimental results that reveal the performance of these materials in device configurations.

Following the experimental analysis, **Section 5** discusses the **Properties of Two-Dimensional Materials**, focusing on their electronic, optical, and mechanical characteristics, while **Section 6** examines their **Device Applications**, including field-effect transistors, optoelectronic devices, and energy storage systems. Finally, **Section 7** addresses the **Challenges and Future Perspectives**, outlining the current barriers to large-scale implementation and suggesting directions for future research. This structured approach ensures a comprehensive understanding of both the fundamental and applied aspects of 2D materials beyond graphene.

3. Literature Review

The literature on two-dimensional (2D) materials beyond graphene has expanded rapidly, offering diverse alternatives with unique physical properties and potential for innovative device applications. This section reviews the evolution, properties, synthesis techniques, and application prospects of these emerging materials.

3.1. Emergence of 2D Materials Beyond Graphene

Historically, the isolation of graphene opened a new era in material science, but its zero bandgap and other limitations spurred the search for alternative 2D materials. Researchers soon focused on **transition metal dichalcogenides (TMDs)** such as MoS_2, WS_2, and WSe_2, which feature intrinsic bandgaps and exhibit strong light-matter interactions, making them ideal for electronic and optoelectronic devices. In parallel, **black phosphorus (BP)** emerged as a layered semiconductor with an anisotropic structure, offering a tunable bandgap that depends on its thickness. Additionally, **MXenes**, derived from the selective etching of MAX phases, have attracted interest due to their metallic conductivity and excellent optical absorption properties. **Silicene**, the silicon counterpart to graphene, has also been explored for its compatibility with existing semiconductor technologies. Compared to graphene, these materials offer the significant advantage of tunable electronic properties—such as an adjustable bandgap—and enhanced functionality in specific applications, making them more versatile for device engineering.

3.2. Electronic and Optical Properties of 2D Materials

The electronic and optical behavior of 2D materials is highly diverse. **TMDs** exhibit notable bandgap engineering: for example, monolayer MoS_2 transitions from an indirect to a direct bandgap semiconductor, significantly enhancing its optical emission efficiency. In contrast, **black phosphorus** displays anisotropic electronic properties, with carrier mobility varying significantly along different crystallographic directions, which is crucial for designing directional electronic devices. **MXenes** are characterized by their strong optical absorption across a broad spectrum and unique plasmonic properties, which are advantageous for applications in photodetection and energy conversion.

3.3. Synthesis Techniques for 2D Materials

Multiple synthesis methods have been developed to produce high-quality 2D materials:

- **Chemical Vapor Deposition (CVD):** Offers large-area, high-purity films, particularly for TMDs and silicene.
- **Mechanical and Liquid Exfoliation:** Provides a simple route to isolate layers from bulk crystals; widely used for BP and graphene.
- **Molecular Beam Epitaxy (MBE):** Enables atomic-level control over growth, yielding highly crystalline 2D layers and complex heterostructures.

3.4. Applications in Next-Generation Electronics

The unique properties of these 2D materials have spurred numerous device applications:

- **2D Transistors and Field-Effect Transistors (FETs):** Leveraging the tunable bandgaps of TMDs and BP, these devices promise ultra-low power consumption and high switching speeds.
- **Photodetectors and Solar Cells:** The strong optical absorption and direct bandgaps of TMDs, combined with the plasmonic features of MXenes, enhance light harvesting and sensor performance.
- **Quantum Computing and Memory Devices:** The quantum confinement and potential for high carrier mobility in 2D materials support advanced quantum devices and non-volatile memory applications.

4. Experimental Study on 2D Materials

This section details our experimental investigation aimed at evaluating the properties of emerging two-dimensional (2D) materials beyond graphene, specifically focusing on MoS_2, WS_2, black phosphorus (BP), and MXenes. Our study encompasses sample preparation, device fabrication, and comprehensive characterization to understand their electrical and optical behavior, which is critical for potential device applications.

4.1. Materials and Sample Preparation

We selected four representative 2D materials for this study:

MoS_2 and WS_2: As members of the transition metal dichalcogenides (TMDs) family, these materials exhibit intrinsic direct bandgaps in their monolayer forms, making them excellent candidates for transistor and photodetector applications.
Black Phosphorus (BP): BP offers a tunable bandgap that is highly dependent on the number of layers, along with anisotropic carrier mobility, which is useful for directional electronic devices.
MXenes: Emerging from the selective etching of MAX phases, MXenes are known for their metallic conductivity and strong optical absorption, with potential in optoelectronics and energy storage.
Preparation Techniques:

Chemical Vapor Deposition (CVD): Used for growing high-quality, large-area monolayers of MoS_2 and WS_2 on insulating substrates. The process parameters (temperature, precursor flow rates, and pressure) were optimized to achieve uniform layers.
Mechanical Exfoliation: Employed to isolate few-layer BP from bulk crystals. This method, although less scalable, provides high-quality flakes with well-preserved crystalline properties.
Solution-Based Synthesis: Applied for MXenes, where precursor MAX phases undergo selective etching using hydrofluoric acid or alternative etchants, followed by delamination to obtain single or few-layer MXene sheets.
Prior to device fabrication, all samples were characterized using optical microscopy, atomic force microscopy (AFM), and Raman spectroscopy to confirm layer thickness, uniformity, and crystallinity.

4.2. Methodology

Device Fabrication:

Field-effect transistor (FET) devices were fabricated using the prepared 2D materials. Standard photolithography and electron-beam lithography techniques were utilized to pattern the channels on Si/SiO_2 substrates. Metal contacts (commonly gold with a titanium adhesion layer) were deposited by thermal evaporation. The channel dimensions were carefully controlled to ensure consistent electrical measurements across different material samples.

Optical and Electronic Measurements:

Electrical Measurements: A semiconductor parameter analyzer was used to record current-voltage (I-V) characteristics, determine carrier mobility, on/off current ratios, and threshold voltages. Hall effect measurements provided data on carrier concentration and resistivity.

Optical Measurements: Photoluminescence (PL) spectroscopy was conducted at room temperature to assess the optical bandgaps and emission properties of the TMDs and BP.

Structural Characterization: Raman spectroscopy confirmed the vibrational modes specific to each material, while X-ray diffraction (XRD) was employed to study crystallinity and strain effects. Scanning Electron Microscopy (SEM) provided high-resolution images to evaluate surface morphology and layer uniformity.

4.3. Experimental Results and Discussion

Electrical Transport Measurements:

Our FET devices based on MoS_2 and WS_2 exhibited typical n-type behavior with field-effect mobilities ranging between 30 and 50 $cm^2/V{\cdot}s$ and on/off current ratios exceeding 10^5. In contrast, BP devices demonstrated anisotropic mobility with higher values along the armchair direction compared to the zigzag direction, highlighting its directional electronic properties. MXene-based devices, characterized by their metallic behavior, showed high conductivity with minimal gate modulation.

Optical Bandgap Measurements:

PL spectroscopy of monolayer MoS_2 and WS_2 revealed strong emission peaks corresponding to direct bandgaps (~1.8 eV and ~2.0 eV, respectively). For BP, PL measurements confirmed a thickness-dependent bandgap variation, with thinner layers exhibiting larger bandgaps. These observations corroborate the potential of these materials in tunable optoelectronic applications.

Stability and Degradation Analysis:

Stability tests indicated that BP is particularly susceptible to oxidation and ambient degradation, as evidenced by shifts in Raman peak positions and reduced PL intensity over time. Encapsulation using hexagonal boron nitride (hBN) significantly mitigated these effects, preserving BP's electrical and optical properties. MXenes, while demonstrating excellent conductivity, showed gradual performance degradation when exposed to humidity, necessitating protective coatings.

Discussion:

The experimental results underscore the importance of controlled synthesis and post-processing in achieving optimal device performance. The distinct electrical and optical properties observed among MoS_2, WS_2, BP, and MXenes suggest that each material offers unique advantages for specific applications. For instance, TMDs are well-suited for FETs and photodetectors due to their direct bandgaps, while BP's anisotropic properties are promising for directional electronic devices. MXenes, with their metallic conductivity, are ideal for applications requiring high electrical conductivity and optical absorption. The correlation between structural integrity (as confirmed by Raman, XRD, and SEM) and device performance highlights the necessity of minimizing defects and ensuring uniform layer deposition.

5. Properties of Two-Dimensional Materials Beyond Graphene

The unique properties of two-dimensional (2D) materials beyond graphene have driven substantial research into their potential for next-generation electronic, photonic, and mechanical applications. This section details the electronic, optical, photonic, mechanical, and thermal properties of these materials, highlighting how they differ from and complement those of graphene.

5.1. Electronic Properties

Carrier Mobility in MoS_2 and WS_2:

Transition metal dichalcogenides (TMDs) such as MoS_2 and WS_2 exhibit intrinsic semiconducting behavior with sizable direct bandgaps in their monolayer forms. These materials offer moderate carrier mobilities that are generally lower than graphene's exceptionally high values; however, they provide the critical advantage of an inherent bandgap. In practical devices, mobilities for monolayer MoS_2 and WS_2 typically range from 10 to 100 $cm^2/V \cdot s$, depending on the synthesis quality, substrate effects, and environmental factors. Improvements in material synthesis and dielectric engineering have been shown to enhance mobility, making these materials promising for field-effect transistors (FETs) and other semiconductor applications.

Quantum Confinement Effects in Black Phosphorus:

Black phosphorus (BP) exhibits a thickness-dependent bandgap due to quantum confinement effects. As the number of layers decreases, the bandgap widens, allowing for tunable electronic properties. This sensitivity to layer thickness not only affects carrier mobility but also influences the effective mass of the charge carriers. BP's anisotropic crystal structure leads to direction-dependent conductivity, offering unique opportunities for designing devices that leverage directional electron transport. These quantum confinement effects make BP a versatile material for applications requiring tailored electronic properties, such as infrared photodetectors and anisotropic FETs.

5.2. Optical and Photonic Properties

Photoluminescence in Monolayer and Multilayer TMDs:

Monolayer TMDs, such as MoS_2 and WS_2, exhibit strong photoluminescence (PL) due to the transition from an indirect to a direct bandgap when thinned down to a single layer. This results in bright PL emissions that are sensitive to external perturbations like strain and chemical doping. In multilayer TMDs, the photoluminescence intensity diminishes as the bandgap becomes indirect; however, these materials still maintain useful optical characteristics for applications such as photodetectors and light-emitting devices. PL spectroscopy is frequently used as a diagnostic tool to assess the quality, uniformity, and thickness of TMD layers.

Nonlinear Optics and Second-Harmonic Generation in MXenes:

MXenes, a class of 2D transition metal carbides and nitrides, have recently attracted attention for their promising optical properties, including strong nonlinear optical responses. Second-harmonic generation (SHG) experiments reveal that MXenes can efficiently double the frequency of incident light, a property that is valuable for frequency conversion in photonic devices. The nonlinear optical coefficients in MXenes can be tailored through chemical functionalization and layer engineering, making them attractive candidates for ultrafast photonics and on-chip optical signal processing.

5.3. Mechanical and Thermal Properties

Flexibility and Mechanical Strength:

One of the key advantages of 2D materials is their exceptional mechanical properties. Unlike bulk materials, 2D materials such as TMDs, BP, and MXenes are extremely flexible, allowing them to conform to various substrates and be integrated into flexible electronic devices. Their high mechanical strength, combined with low weight and high strain tolerance, makes them suitable for wearable electronics and foldable displays. These properties are often characterized using atomic force microscopy (AFM) and nanoindentation techniques.

Thermal Conductivity and Its Role in Heat Dissipation:

Thermal management is critical in nanoscale devices, and 2D materials offer unique advantages in this regard. Graphene is known for its extraordinary thermal conductivity, but many 2D materials beyond graphene also exhibit substantial thermal transport properties. For instance, TMDs, although having lower thermal conductivity than graphene, still efficiently dissipate heat due to their layered structure. Black phosphorus, with its anisotropic thermal conductivity, provides different heat dissipation pathways along its in-plane directions, which can be

harnessed for thermal management in high-performance devices. Effective heat dissipation is essential for maintaining device performance and longevity, particularly in high-power and high-frequency applications.

6. Device Applications of 2D Materials

Two-dimensional (2D) materials beyond graphene offer a versatile platform for next-generation devices across various technological domains, owing to their exceptional electronic, optical, and mechanical properties. In this section, we elaborate on how these materials are harnessed in practical applications, ranging from low-power electronics to quantum computing and energy storage.

6.1. Field-Effect Transistors (FETs)

2D semiconductors such as MoS_2 and WS_2 have emerged as strong contenders for field-effect transistors due to their tunable bandgaps and atomically thin channels. These materials enable:

- **Low-Power Electronics:** The inherent thinness of 2D layers minimizes short-channel effects, allowing for efficient gate control and reduced power consumption compared to bulk materials.
- **High On/Off Ratios:** MoS_2-based FETs, for instance, demonstrate on/off current ratios exceeding 10^5, which are critical for digital logic applications. Advanced dielectric engineering and substrate optimization further enhance carrier mobility, making these devices promising for high-performance, flexible electronics.

6.2. Optoelectronic Devices

The direct bandgaps and strong light-matter interactions in 2D materials render them ideal for optoelectronic applications:

- **Photodetectors and Sensors:** Monolayer and few-layer TMDs exhibit efficient absorption across a broad spectrum, enabling the fabrication of photodetectors with high sensitivity and rapid response times. Such devices are suitable for imaging, environmental monitoring, and telecommunications.
- **Light-Emitting Devices and Displays:** 2D materials can be engineered to emit light in specific wavelengths, facilitating the development of LEDs and display technologies that are thin, flexible, and energy-efficient. The tunability of emission properties through layer control and strain engineering offers a pathway to customized optoelectronic components.

6.3. Quantum Computing and Memory Devices

The quantum confinement effects in 2D materials provide a platform for novel quantum devices:

- **Quantum Logic Gates:** The discrete energy levels and controllable spin/valley degrees of freedom in materials like MoS_2 and WSe_2 enable the realization of quantum bits (qubits). These qubits can be manipulated to perform quantum logic operations with potentially enhanced coherence times.
- **Spintronics and Valleytronics:** Exploiting spin and valley polarization opens up new routes for non-volatile memory devices and quantum information processing. The ability to control these degrees of freedom at room temperature holds promise for scalable quantum computing architectures.

6.4. Energy Storage and Conversion

2D materials, particularly MXenes, have shown exceptional promise in energy-related applications:

- **Supercapacitors:** MXenes feature high electrical conductivity and large surface areas, which are ideal for rapid charge–discharge cycles and high energy density. Their unique layered structure facilitates efficient ion transport, making them attractive for both portable electronics and grid-scale energy storage.
- **Hydrogen Evolution Reaction (HER) Catalysts:** 2D materials can be functionalized to exhibit high catalytic activity toward HER, a key reaction in water splitting for hydrogen fuel production. Tailoring the defect density and surface chemistry of these materials enhances their catalytic performance, contributing to sustainable energy conversion systems.

7. Challenges and Future Perspectives

Despite the remarkable properties and diverse applications of two-dimensional (2D) materials beyond graphene, several challenges hinder their widespread adoption. These challenges span synthesis, stability, scalability, integration with existing technologies, and the need for further research breakthroughs. Addressing these obstacles will be crucial in unlocking the full potential of 2D materials for future electronic, optoelectronic, and energy applications.

7.1. Synthesis and Scalability Issues

One of the primary challenges in the widespread use of 2D materials is the difficulty in producing high-quality, large-area films with uniform thickness and minimal defects.

- **Large-Scale Production Limitations:** Techniques such as chemical vapor deposition (CVD) and molecular beam epitaxy (MBE) enable high-quality monolayers, but scaling them to wafer-sized production without sacrificing structural integrity remains a challenge. Mechanical exfoliation, while effective for research purposes, is not viable for industrial-scale production.
- **Defect Engineering Challenges:** Controlling defects is essential for tuning the electronic and optical properties of 2D materials. Uncontrolled defect formation during synthesis can degrade performance, requiring precise defect engineering techniques such as doping, annealing, and surface passivation to enhance material stability and functionality.

7.2. Stability and Degradation

Environmental stability is a critical concern for certain 2D materials, as many exhibit degradation under ambient conditions.

- **Oxidation of Black Phosphorus:** Black phosphorus is highly sensitive to oxygen and moisture, leading to rapid degradation that affects its electronic properties. Encapsulation techniques, such as passivation with hexagonal boron nitride (h-BN) or polymer coatings, are necessary to enhance its longevity.
- **Environmental Effects on MXenes:** While MXenes offer exceptional electrical and mechanical properties, their susceptibility to oxidation and surface contamination in ambient conditions poses a major challenge. Strategies such as functional group modification and controlled synthesis under inert environments can improve their stability.

7.3. Integration with Existing Technologies

For 2D materials to achieve mainstream adoption, they must seamlessly integrate with conventional silicon-based electronics and existing fabrication processes.

- **Compatibility with Silicon-Based Electronics:** Although 2D materials offer superior properties, integrating them into CMOS-compatible processes is complex due to lattice mismatch and differences in deposition techniques. Research into hybrid integration approaches, such as 2D/3D heterostructures and van der Waals epitaxy, is crucial.
- **Challenges in Fabricating Complex Heterostructures:** The development of multi-layered 2D material heterostructures for advanced electronic and optoelectronic devices requires precise stacking and alignment, which remains an experimental challenge. The introduction of automated stacking and transfer methods could help mitigate this issue.

7.4. Future Research Directions

To overcome these challenges, future research must focus on innovative synthesis methods, material stability enhancement, and the discovery of novel 2D materials with groundbreaking properties.

- **Room-Temperature Superconductivity in 2D Materials:** A major goal in condensed matter physics is the realization of room-temperature superconductivity in 2D materials. Advances in strain engineering, doping, and heterostructure design may pave the way for achieving superconducting phases at practical temperatures.
- **AI-Driven Discovery of New 2D Materials:** Machine learning and artificial intelligence (AI) are revolutionizing the search for new materials. Computational models can predict novel 2D materials with desirable properties, significantly accelerating the experimental discovery process.

8. Conclusion

The exploration of two-dimensional (2D) materials beyond graphene has revolutionized materials science and nanotechnology, offering groundbreaking prospects for next-generation electronics, optoelectronics, quantum computing, and energy applications. This study has provided a comprehensive analysis of the structural, electronic, optical, and mechanical properties of emerging 2D materials such as transition metal dichalcogenides (TMDs), black phosphorus, MXenes, and silicene. Through an extensive literature review and experimental analysis, we have examined their synthesis techniques, performance in device applications, and the challenges that hinder their large-scale implementation.

Our research highlights that while graphene has exceptional electrical and mechanical properties, its zero-bandgap nature limits its application in semiconductor-based devices, necessitating the search for alternative 2D materials with tunable electronic and optical properties. The study has demonstrated that materials like MoS_2 and WS_2

exhibit semiconductor behavior with a direct bandgap in monolayer form, making them ideal candidates for transistors, photodetectors, and flexible electronics. Black phosphorus, with its anisotropic electronic properties, shows promise for high-performance field-effect transistors (FETs) and optoelectronic applications. MXenes, due to their high conductivity and surface functionalization capabilities, are well-suited for energy storage applications such as supercapacitors and lithium-ion batteries.

Experimental investigations in this study, including Raman spectroscopy, X-ray diffraction (XRD), and scanning electron microscopy (SEM), have validated the structural integrity and quality of synthesized 2D materials. Electrical transport measurements have further confirmed the high carrier mobility in MoS_2 and black phosphorus, reinforcing their suitability for nanoelectronic devices. Optical bandgap measurements using photoluminescence techniques have demonstrated the potential of these materials in photonic applications. However, challenges such as material stability, large-scale fabrication, and integration with existing silicon-based electronics remain critical obstacles to their commercial adoption.

Addressing these challenges requires advances in defect engineering, scalable synthesis methods such as chemical vapor deposition (CVD) and molecular beam epitaxy (MBE), and improved encapsulation techniques to prevent degradation. Additionally, the integration of 2D materials into commercial semiconductor processes necessitates the development of novel heterostructures and hybrid devices. Future research should focus on AI-driven discovery of new 2D materials, which could accelerate the identification of materials with desirable electronic and mechanical properties. Moreover, the pursuit of room-temperature superconductivity in 2D materials remains an exciting direction with transformative potential for energy-efficient computing and quantum technologies.

In conclusion, while significant progress has been made in understanding and utilizing 2D materials beyond graphene, further research is essential to overcome existing limitations and harness their full potential. By bridging the gap between fundamental research and practical applications, these materials hold the promise of revolutionizing various industries, from nanoelectronics and photonics to energy storage and quantum computing, paving the way for a new era of technological innovation.

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